

APPENDIX B

VERSION WITH MARKINGS TO SHOW CHANGES MADE

37 C.F.R. § 1.121(b)(iii) AND (c)(ii)

CLAIMS:

1. (Thrice Amended) A semiconductor device comprising, in combination, a silicon substrate having a first and second surface; a first layer disposed on said first surface and having impurities of the n or p conductivity type uniformly distributed throughout the volume of said first layer; a second layer disposed on said first layer; said second layer having impurities of the same type as those in said first layer uniformly distributed therethrough and having a substantially uniform resistivity; the concentration of impurities in said second layer being greater than the concentration of impurities in said first layer; [said first surface, said first layer and said second layer having generally coincident boundaries;] a plurality of diffusions of a conductivity type opposite to that of said second layer uniformly distributed into the surface of said second layer and defining p-n junctions therein; and[;] said first layer and said second layer being epitaxial silicon layers.